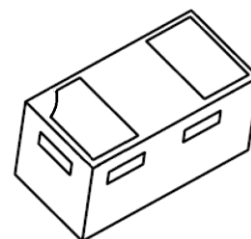


Product Summary

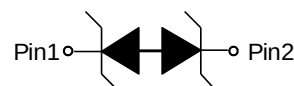
The GESDBL5V0Y1 is designed to protect voltage sensitive electronic components from ESD and other transients. Excellent clamping capability, low leakage, low capacitance, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in digital cameras, cellular phones, MP3 players and many other portable applications where board space is at a premium.

Feature

- Low reverse stand-off voltage: 5V Max.
- Low reverse clamping voltage
- Ultra-low leakage current
- Fast response time
- IEC 61000-4-2 Level 4 ESD protection

DFN1006-2L


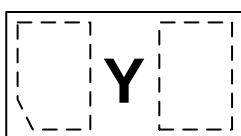
Schematic diagram



Application

- Digital cameras
- Portable applications
- Audio and video equipment
- MP3 players
- Mobile phone

Marking:



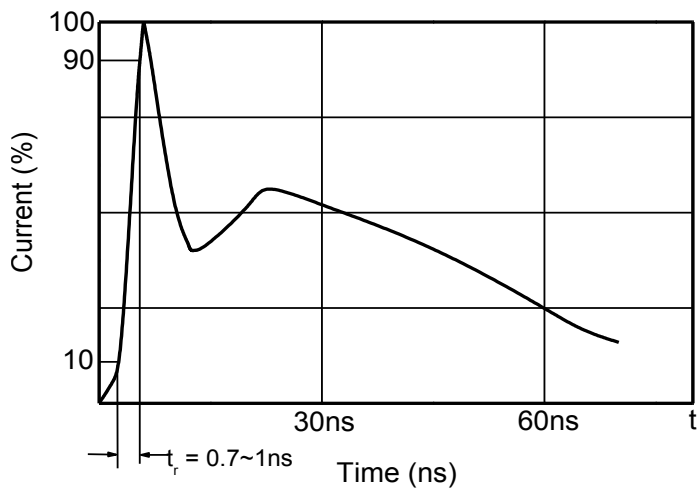
Front Side

Y=Device Code

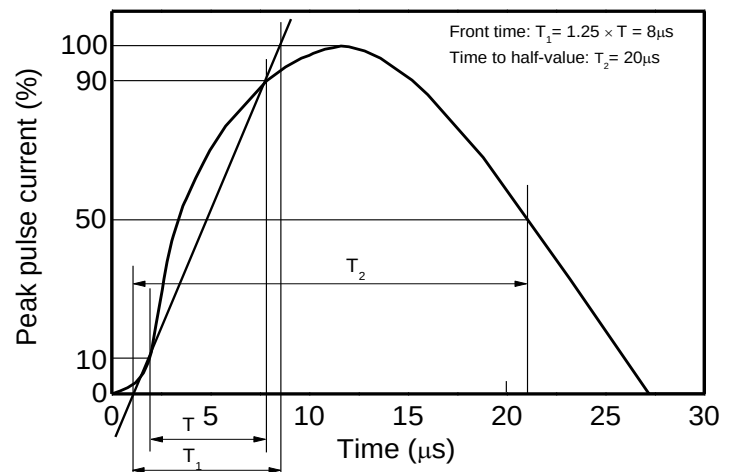
Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
IEC 61000-4-2 ESD Voltage Air Model	V_{ESD}	± 30	kV
IEC 61000-4-2 ESD Voltage Contact Model		± 30	
JESD22-A114-B ESD Voltage Per Human Body Model		± 16	
ESD Voltage Machine Model		± 0.4	
Peak Pulse Power (8/20 μ s)	P_{pk}	100	W
Peak Pulse Current (8/20 μ s)	I_{PP}	8	A
Junction Temperature	T_J	-55~ +125	°C
Storage Temperature	T_{stg}	-55~ +150	°C

Contact discharge current waveform per IEC61000-4-2

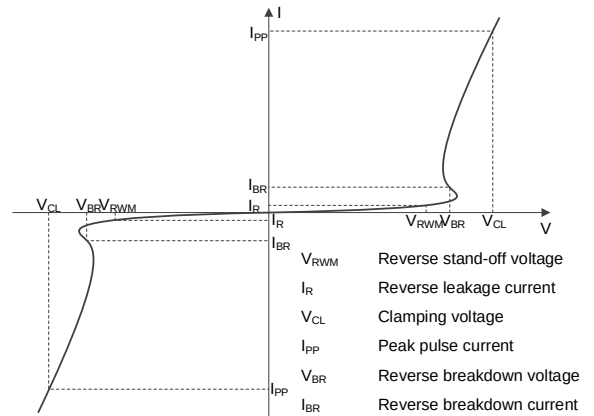


8/20 μ s waveform per IEC61000-4-5



Electrical Parameter

Symbol	Parameter
V_C	Clamping Voltage @ I_{PP}
I_{PP}	Peak Pulse Current
V_{BR}	Breakdown Voltage @ I_{BR}
I_{BR}	Test Current
I_R	Reverse Leakage Current @ V_{RWM}
V_{RWM}	Reverse Standoff Voltage

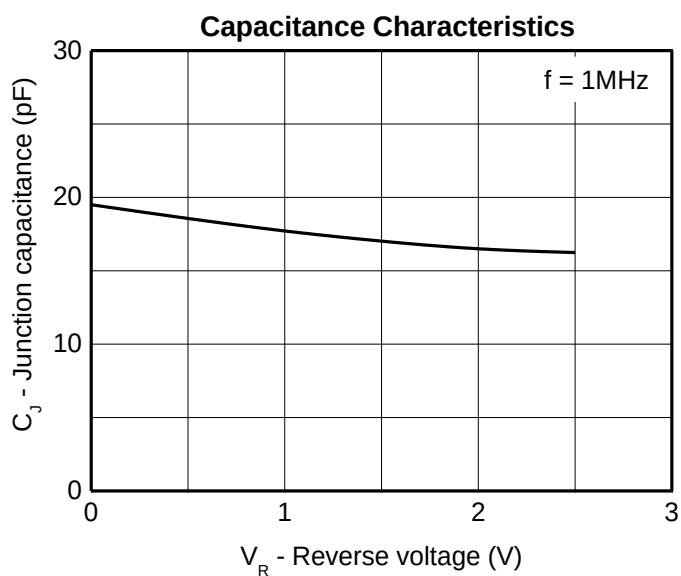
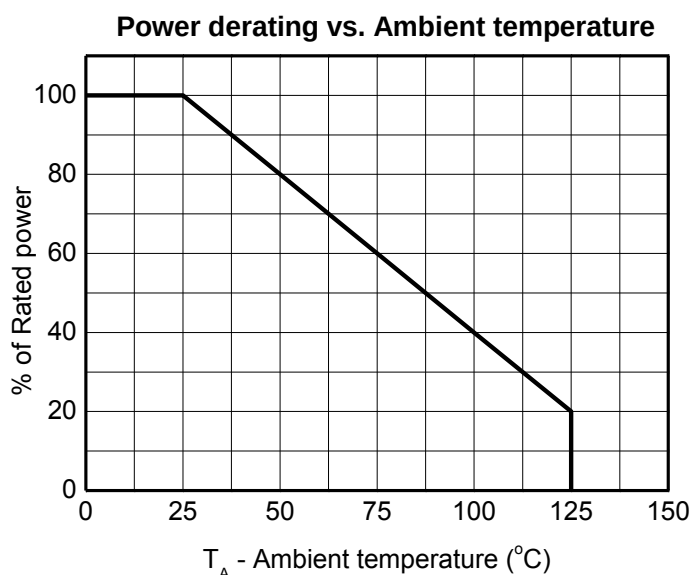
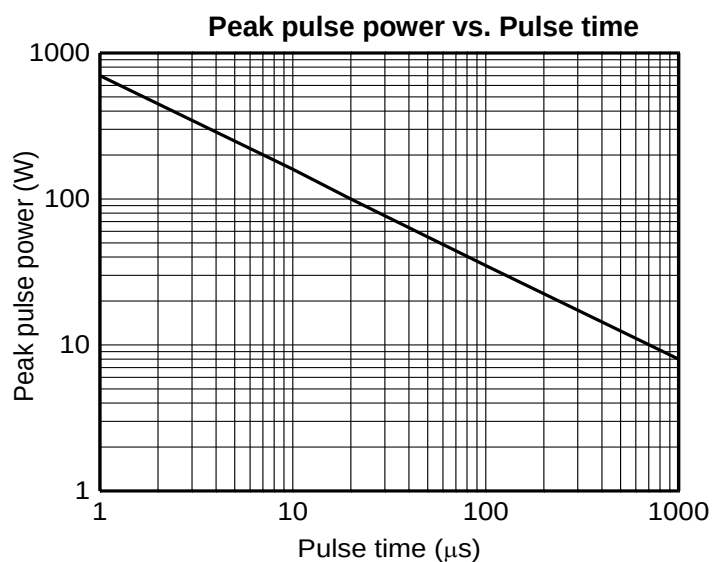
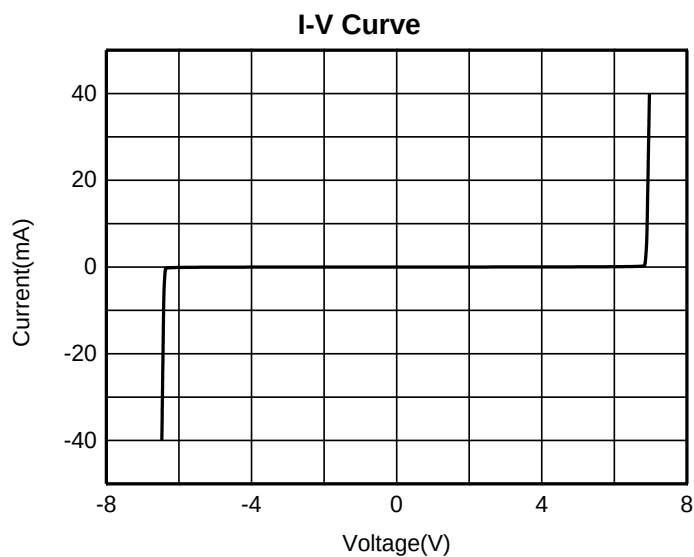
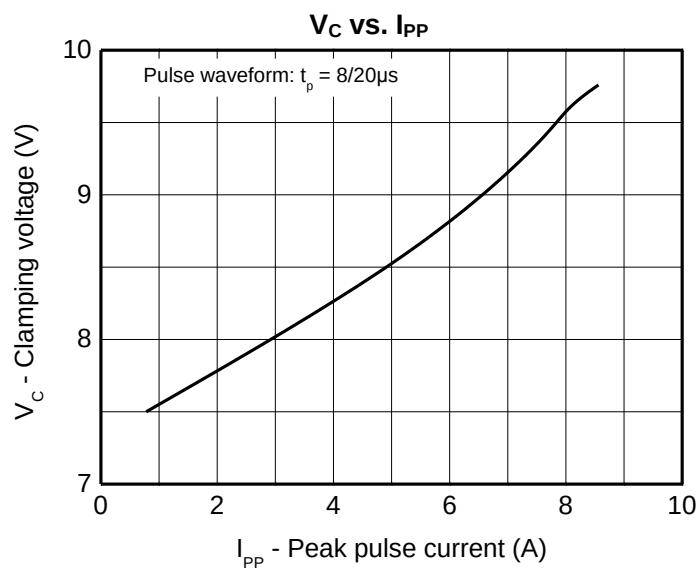


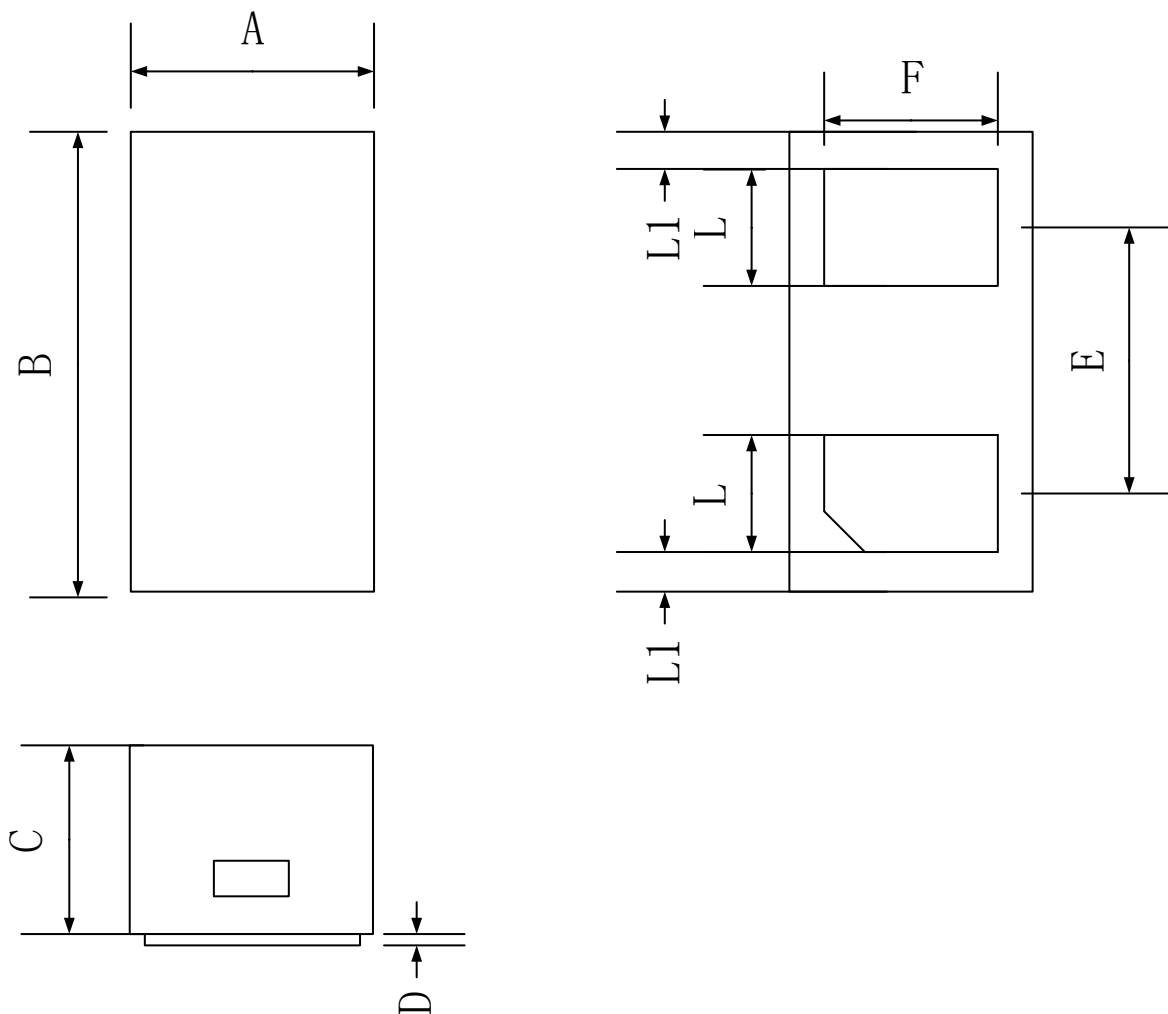
V-I characteristics for a Bi-directional TVS

Electrical Characteristics ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse stand-off voltage	V_{RWM}				5	V
Reverse leakage current	I_R	$V_{RWM}=5V$			0.5	μA
Breakdown voltage	$V_{(BR)}$	$I_T=1mA$	5.6		7.4	V
Clamping voltage	V_{C1}	$I_{PP} = 1A$ (8 x 20 μs pulse)		7	8	V
	V_{C2}	$I_{PP} = 8A$ (8 x 20 μs pulse)		10	12.5	V
Junction capacitance	C_j	$V_R=0V, f=1MHz$		17	22	pF

Typical Characteristics



DFN1006-2L Package Outline Dimensions


	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	0.55	0.60	0.68
B	0.95	1.00	1.08
C	0.44	0.47	0.50
D	0.00	0.03	0.05
E	-	0.65	-
F	0.40	0.50	0.60
L	0.20	0.25	0.30
L1	0.05REF		